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• Supplementary File •

The Mechanism of Photocarrier Transport in Vacuum Ultraviolet Photodetector based on Hexagonal Boron Nitride Nanosheets

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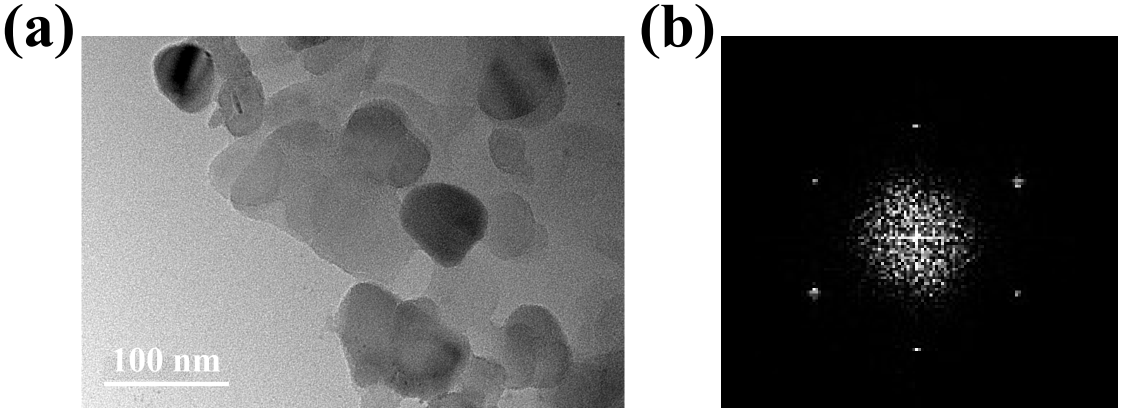

Figure S1 (a) TEM image of BNNSs. (b) FFT pattern.

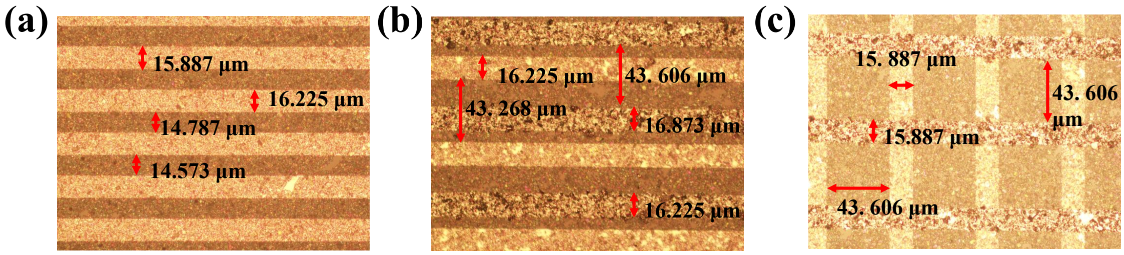

Figure S2 Electrode dimensions and optical microscope images. (a) PD 1. (b) PD 2. (c) PD 3.

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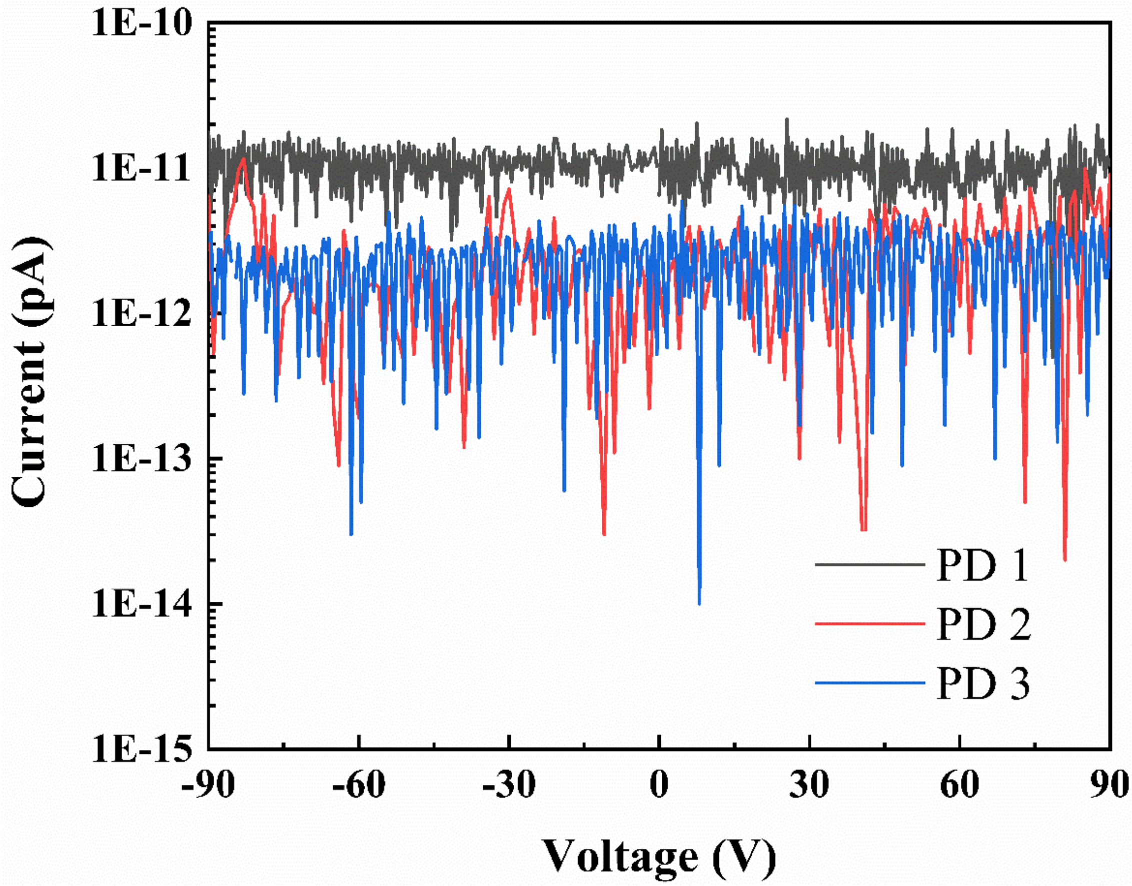

Figure S3 Dark current-voltage characteristic curves (logarithmic coordinate).

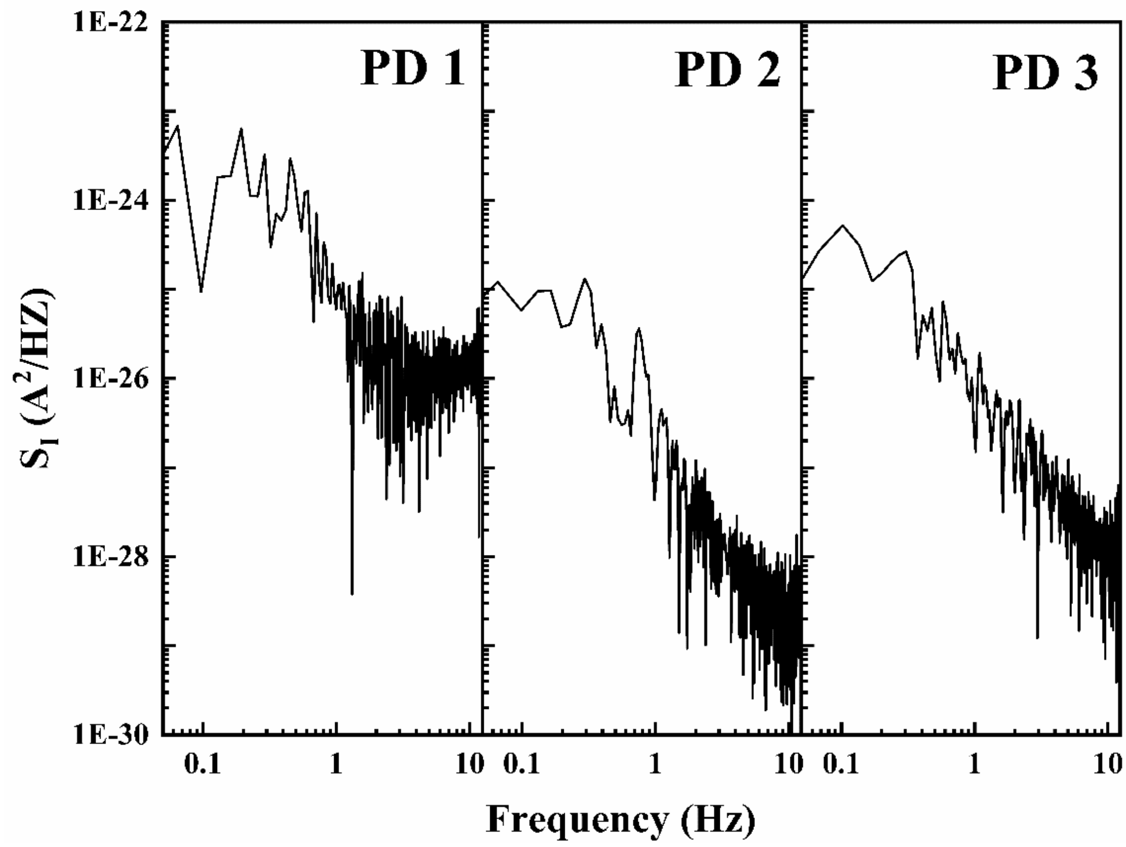

Figure S4 Noise power spectral density (S_I) of PD 1–PD 3.

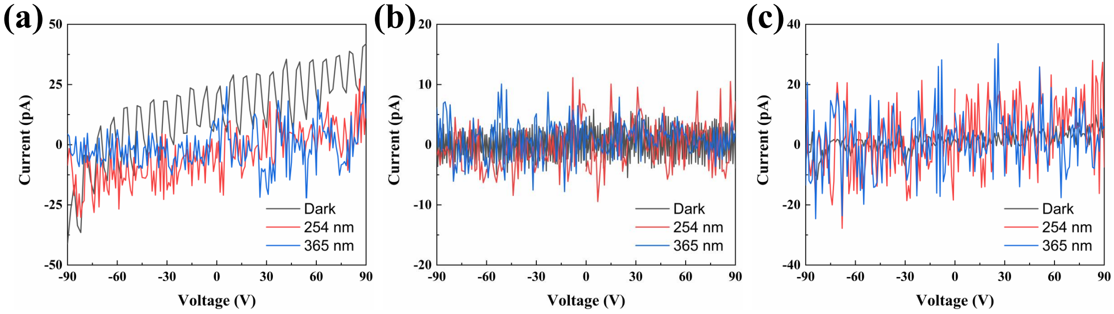

Figure S5 *I–V* curves of (a) PD 1, (b) PD 2, and (c) PD 3 under dark conditions and illumination at 254 nm and 365 nm.